

BCR5KM-14LC

Triac

Medium Power Use

REJ03G0332-0200

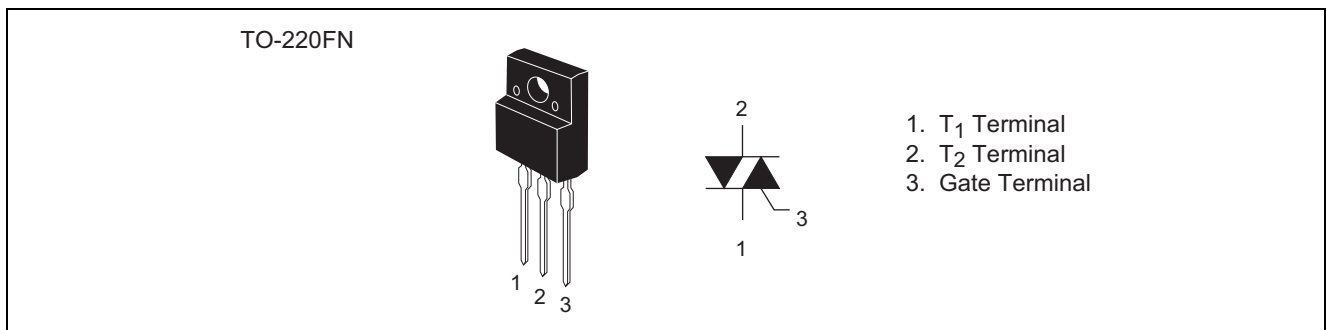
Rev.2.00

Dec.17.2004

Features

- $I_{T(RMS)}$: 5 A
- V_{DRM} : 700 V
- I_{FGTI} , I_{RGTI} , I_{RGT} : 50 mA
- V_{ISO} : 2000 V
- The product guaranteed maximum junction temperature 150°C.
- Insulated Type
- Planar Passivation Type

Outline



Applications

Motor control, heater control

Maximum Ratings

Parameter	Symbol	Voltage class	Unit
		14	
Repetitive peak off-state voltage ^{Note1}	V_{DRM}	700	V
Non-repetitive peak off-state voltage ^{Note1}	V_{DSM}	800	V

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I_T (RMS)	5	A	Commercial frequency, sine full wave 360° conduction, $T_c = 116^\circ\text{C}$
Surge on-state current	I_{TSM}	30	A	60Hz sinewave 1 full cycle, peak value, non-repetitive
I^2t for fusing	I^2t	3.7	A^2s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P_{GM}	5	W	
Average gate power dissipation	$P_{G(AV)}$	0.5	W	
Peak gate voltage	V_{GM}	10	V	
Peak gate current	I_{GM}	2	A	
Junction temperature	T_j	- 40 to +150	$^\circ\text{C}$	
Storage temperature	T_{stg}	- 40 to +150	$^\circ\text{C}$	
Mass	—	2.0	g	Typical value
Isolation voltage	V_{iso}	2000	V	$T_a = 25^\circ\text{C}$, AC 1 minute, $T_1 \cdot T_2 \cdot G$ terminal to case

Notes: 1. Gate open.

Electrical Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Repetitive peak off-state current	I_{DRM}	—	—	2.0	mA	$T_j = 125^\circ\text{C}$, V_{DRM} applied
On-state voltage	V_{TM}	—	—	1.8	V	$T_c = 25^\circ\text{C}$, $I_{TM} = 7\text{ A}$, Instantaneous measurement
Gate trigger voltage ^{Note2}	I	V_{FGTI}	—	—	1.5	$T_j = 25^\circ\text{C}$, $V_D = 6\text{ V}$, $R_L = 6\ \Omega$, $R_G = 330\ \Omega$
	II	V_{RGTI}	—	—	1.5	
	III	V_{RGTIII}	—	—	1.5	
Gate trigger current ^{Note2}	I	I_{FGTI}	—	—	50	$T_j = 25^\circ\text{C}$, $V_D = 6\text{ V}$, $R_L = 6\ \Omega$, $R_G = 330\ \Omega$
	II	I_{RGTI}	—	—	50	
	III	I_{RGTIII}	—	—	50	
Gate non-trigger voltage	V_{GD}	0.2	—	—	V	$T_j = 125^\circ\text{C}$, $V_D = 1/2 V_{DRM}$
Thermal resistance	$R_{th(j-c)}$	—	—	4.2	$^\circ\text{C/W}$	Junction to case ^{Note3}
Critical-rate of rise of off-state commutating voltage ^{Note4}	$(dv/dt)_c$	5	—	—	$\text{V}/\mu\text{s}$	$T_j = 125^\circ\text{C}$

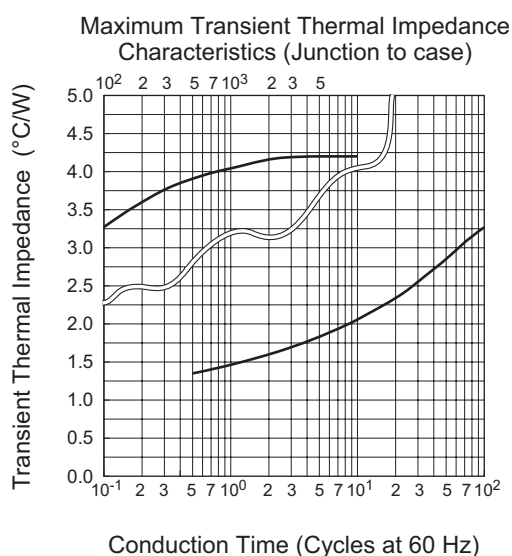
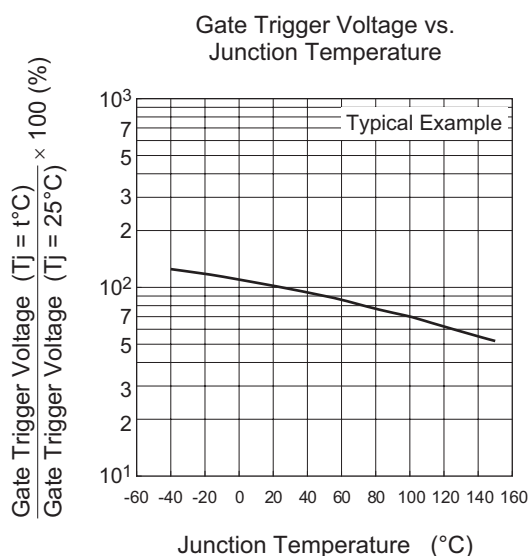
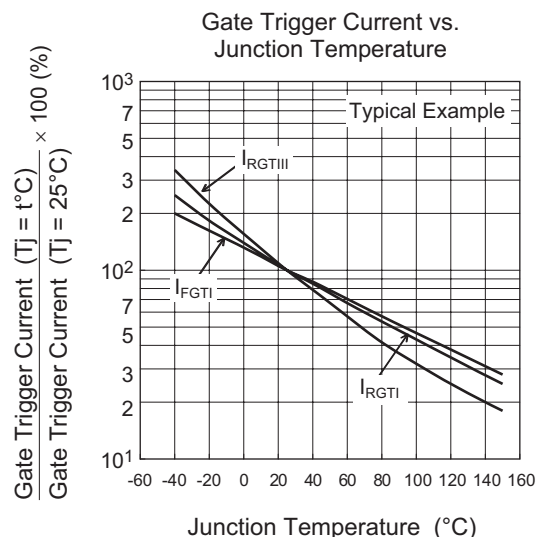
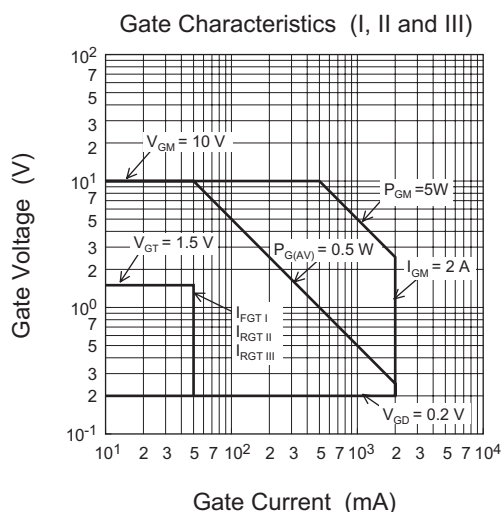
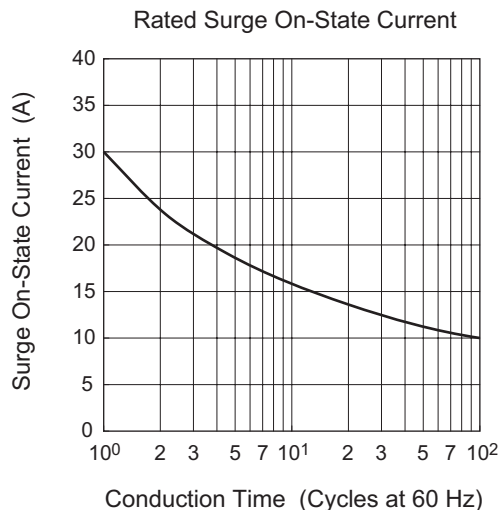
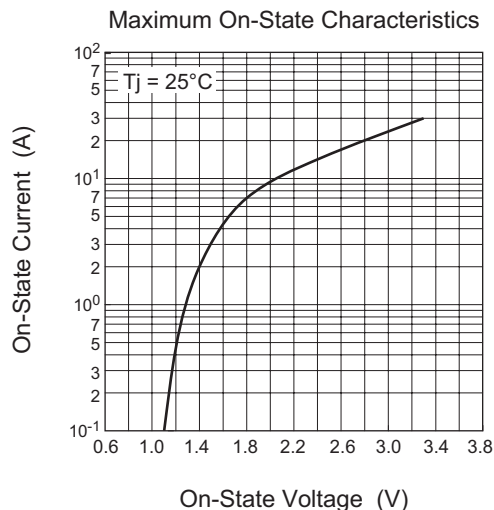
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

3. The contact thermal resistance $R_{th(c-f)}$ in case of greasing is 0.5°C/W .

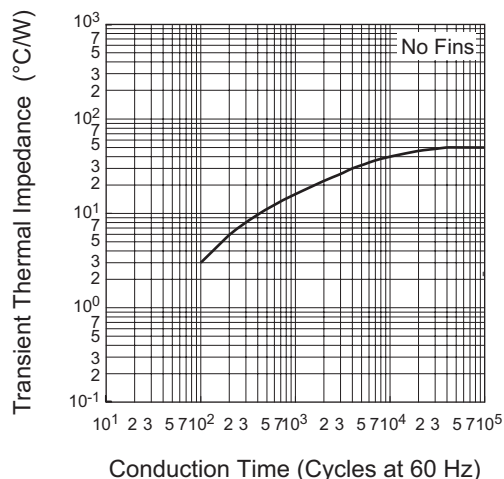
4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature $T_j = 125^\circ\text{C}$ 2. Rate of decay of on-state commutating current $(di/dt)_c = -2.5\text{ A/ms}$ 3. Peak off-state voltage $V_D = 400\text{ V}$	

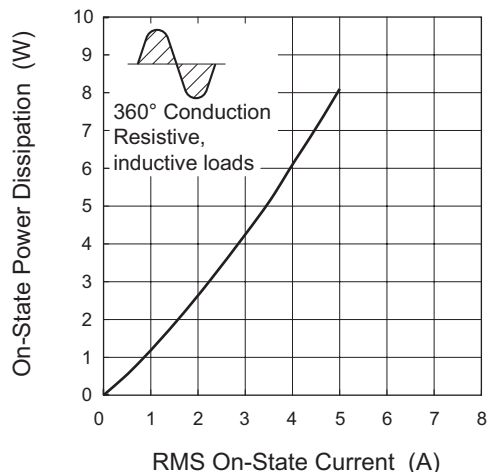
Performance Curves



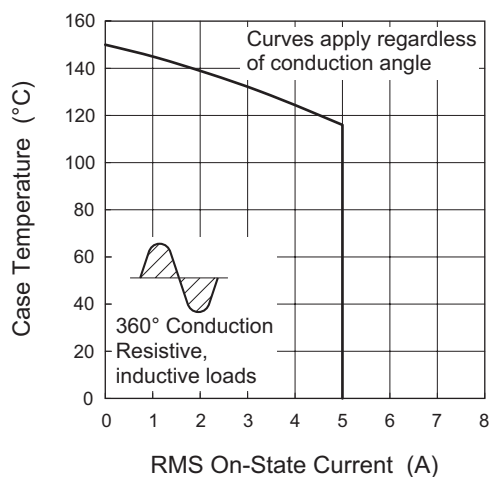
Maximum Transient Thermal Impedance Characteristics (Junction to ambient)



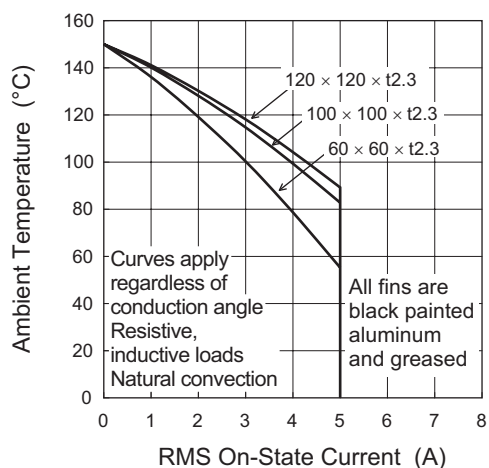
Maximum On-State Power Dissipation



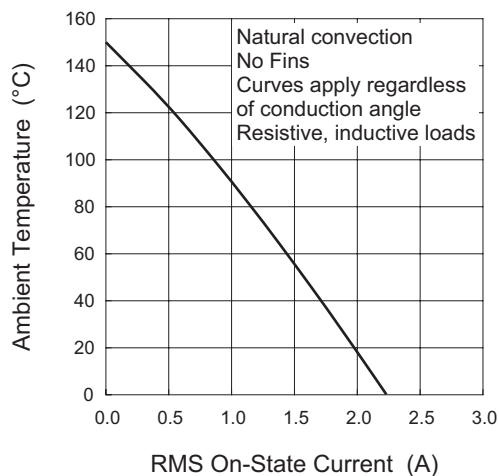
Allowable Case Temperature vs. RMS On-State Current



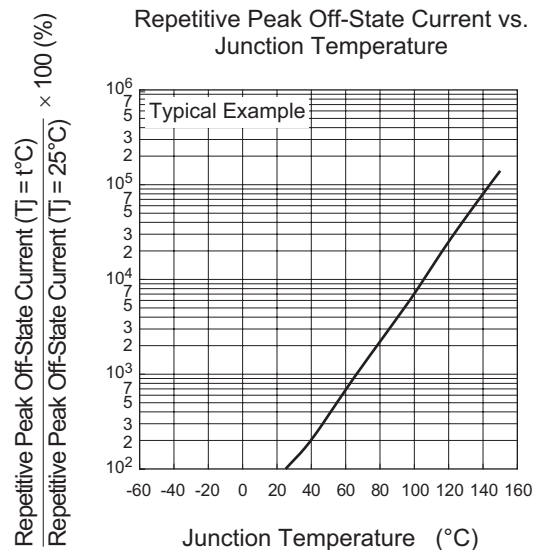
Allowable Ambient Temperature vs. RMS On-State Current

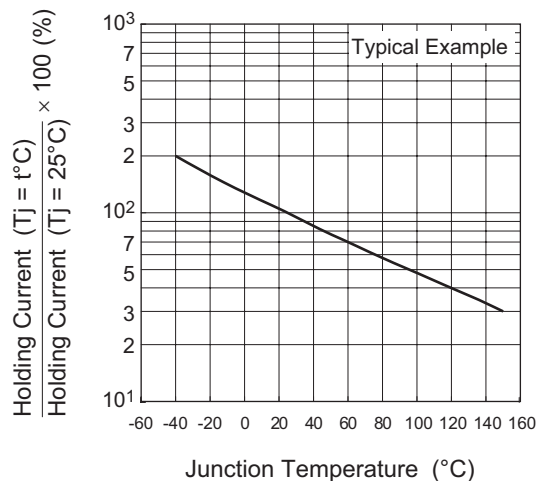
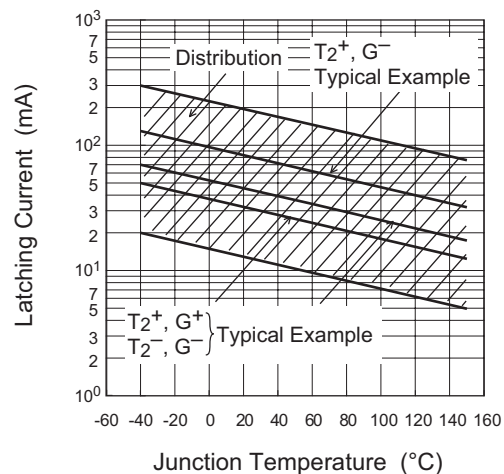
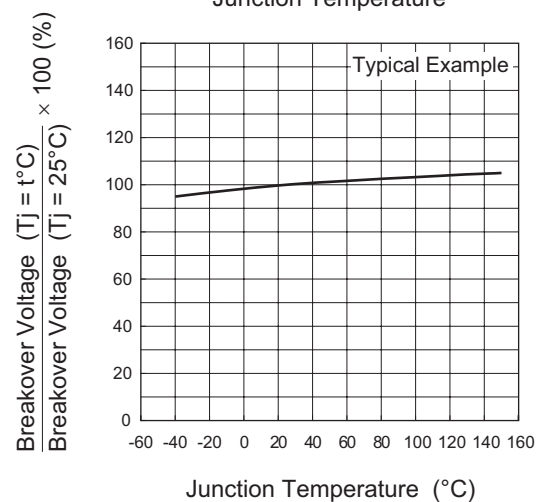
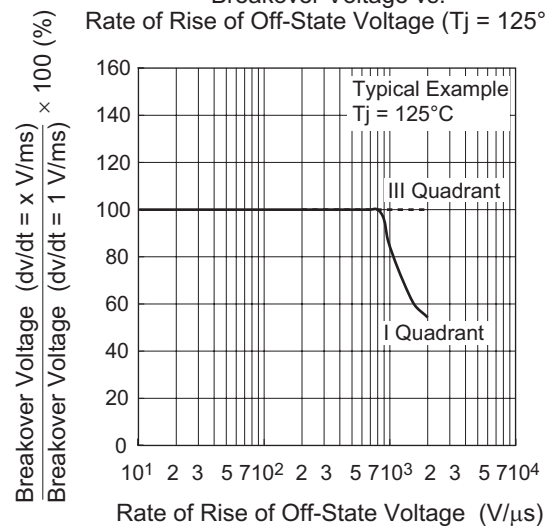
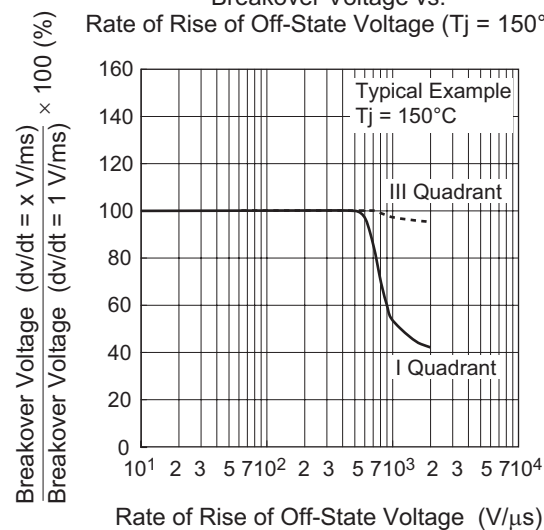
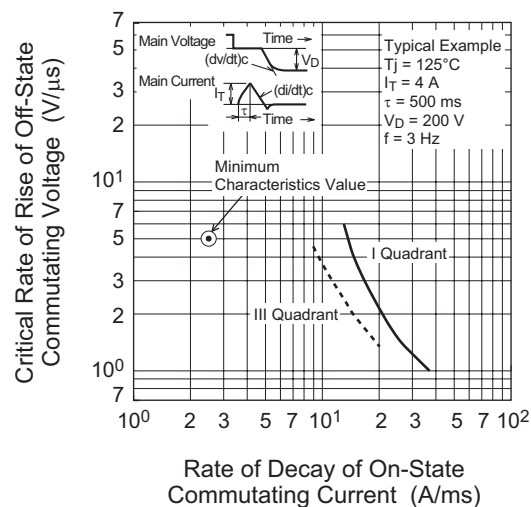


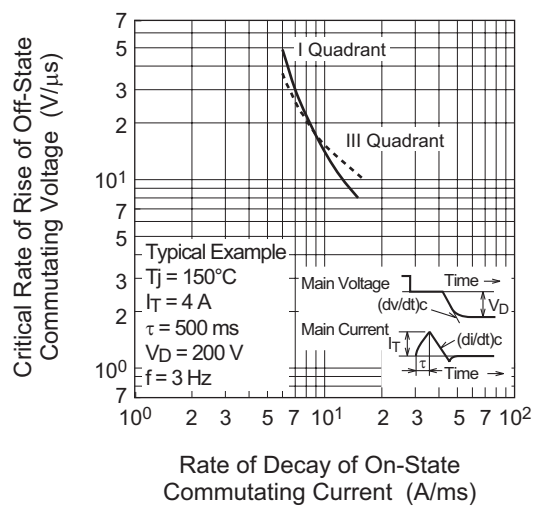
Allowable Ambient Temperature vs. RMS On-State Current



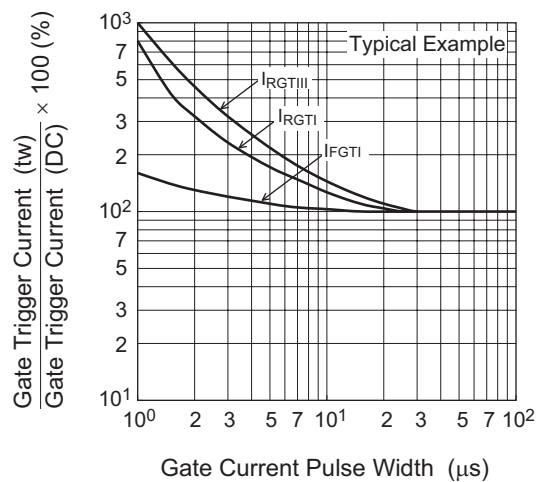
Repetitive Peak Off-State Current vs. Junction Temperature



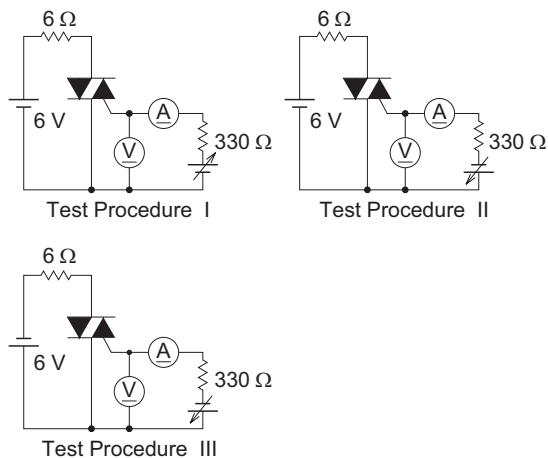
Holding Current vs.
Junction TemperatureLatching Current vs.
Junction TemperatureBreakover Voltage vs.
Junction TemperatureBreakover Voltage vs.
Rate of Rise of Off-State Voltage ($T_j = 125^\circ\text{C}$)Breakover Voltage vs.
Rate of Rise of Off-State Voltage ($T_j = 150^\circ\text{C}$)Commutation Characteristics ($T_j = 125^\circ\text{C}$)

Commutation Characteristics ($T_j = 150^\circ\text{C}$)

Gate Trigger Current vs. Gate Current Pulse Width



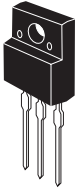
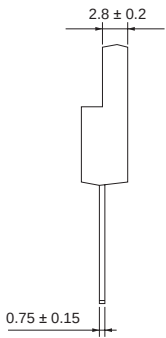
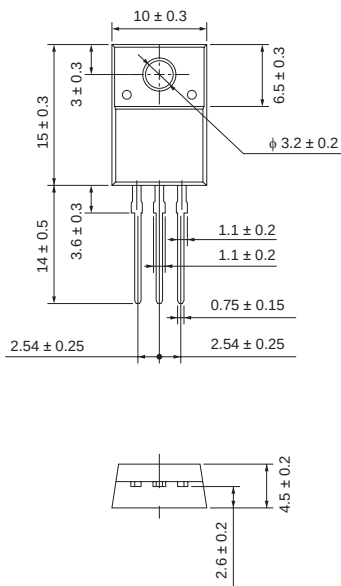
Gate Trigger Characteristics Test Circuits



Package Dimensions

TO-220FN

EIAJ Package Code	JEDEC Code	Mass (g) (reference value)	Lead Material
—	—	2.0	Cu alloy



Note 1) The dimensional figures indicate representative values unless otherwise the tolerance is specified.

Symbol	Dimension in Millimeters		
	Min	Typ	Max
A	—	—	—
A ₁	—	—	—
A ₂	—	—	—
b	—	—	—
D	—	—	—
E	—	—	—
e	—	—	—
x	—	—	—
y	—	—	—
y ₁	—	—	—
ZD	—	—	—
ZE	—	—	—

Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Tube	50	Type name	BCR5KM-14LC
Lead form	Tube	50	Type name – Lead forming code	BCR5KM-14LC-A8

Note : Please confirm the specification about the shipping in detail.

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